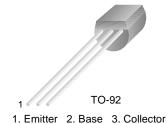


## KSP55/56

### **Amplifier Transistor**

- Collector-Emitter Voltage: V<sub>CEO</sub>=KSP55: 60V KSP56: 80V
- Collector Power Dissipation: P<sub>C</sub> (max) =625mW
- Complement to KSP05/06



# **PNP Epitaxial Silicon Transistor**

## Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: KSP55	-60	V
	: KSP56	-80	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: KSP55	-60	V
	: KSP56	-80	V
V <sub>CEO</sub>	Emitter-Base Voltage	-4	V
I <sub>C</sub>	Collector Current	-500	mA
P <sub>C</sub>	Collector Power Dissipation	625	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	* Collector-Emitter Breakdown Voltage : KSP55 : KSP56	I <sub>C</sub> = -1mA, I <sub>B</sub> =0	-60 -80		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-4		V
I <sub>CBO</sub>	Collector Cut-off Current : KSP55 : KSP56	$V_{CB}$ = -60V, $I_{E}$ =0 $V_{CB}$ = -80V, $I_{E}$ =0		-0.1 -0.1	μ <b>Α</b> μ <b>Α</b>
I <sub>CEO</sub>	Collector Cut-off Current	V <sub>CE</sub> = -60V, I <sub>B</sub> =0		-0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -1V, I <sub>C</sub> = -10mA V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA	50 50		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA		-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -2V, I <sub>C</sub> = -10mA f=100MHz	50		MHz

\* Pulse Test: PW≤300μs, Duty Cycle≤2%

## **Typical Characteristics**

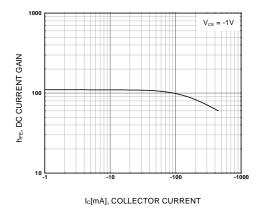


Figure 1. DC current Gain

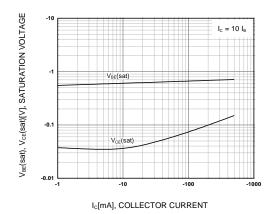


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

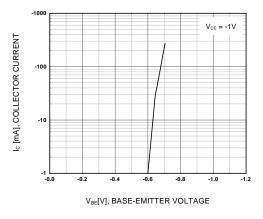


Figure 3. Base-Emitter On Voltage

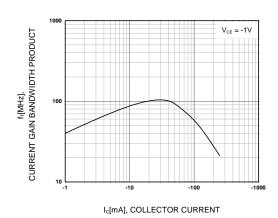
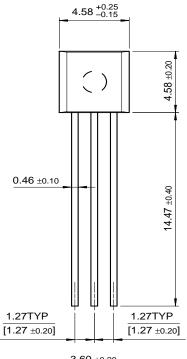
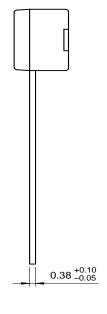


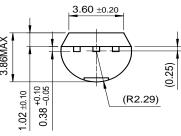
Figure 4. Current Gain Bandwidth Product

# **Package Dimensions**

TO-92







Dimensions in Millimeters

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EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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